

PHASE CHANGEABLE LAYERS INCLUDING PROTRUDING PORTIONS IN
ELECTRODES THEREOF AND METHODS OF FORMING SAME

ABSTRACT

5 A structure in a phase changeable memory cell can include a bottom electrode
having an interlayer dielectric layer thereon, the bottom electrode can have a recess
therein that extends beyond a boundary between the bottom electrode and the
interlayer dielectric. A phase changeable layer can be formed in the recess and
include a protruding portion of the phase changeable layer that protrudes into the
10 bottom electrode beyond the boundary. Related methods are also disclosed.